# **Dual Common Base-Collector Bias Resistor Transistors**

### NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. The NSTB1005DXV5T1 contains two complementary BRT devices are housed in the SOT-553 package which is ideal for low power surface mount applications where board space is at a premium.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch Tape and Reel
- This is a Pb-Free Device

**MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$  unless otherwise noted, common for  $Q_1$  and  $Q_2$ , – minus sign for  $Q_1$  (PNP) omitted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	Ic	100	mAdc

#### THERMAL CHARACTERISTICS

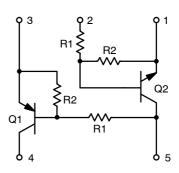
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 1)  Derate above 25°C (Note 1)	P <sub>D</sub>	357 2.9	mW mW/°C
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic			
(Both Junctions Heated)	Symbol	Max	Unit
(Both Junctions Heated)  Total Device Dissipation  T <sub>A</sub> = 25°C (Note 1)  Derate above 25°C (Note 1)	Symbol P <sub>D</sub>	<b>Max</b> 500 4.0	mW mW/°C
Total Device Dissipation T <sub>A</sub> = 25°C (Note 1)	-	500	mW

<sup>1.</sup> FR-4 @ Minimum Pad



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#### **MARKING DIAGRAM**



UC = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

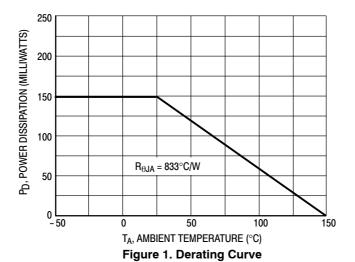
Device	Package	Shipping <sup>†</sup>		
NSTB1005DXV5T1G	SOT-553 (Pb-Free)	4000/Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

1

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Q1 TRANSISTOR: PNP - OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	_	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter–Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}, I_{C} = 0$ )	I <sub>EBO</sub>	-	-	0.1	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS	•				
DC Current Gain	h <sub>FE</sub>	80	140	-	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>E</sub> = 0.3 mA)	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC}$ = 5.0 V, $V_B$ = 0.5 V, $R_L$ = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	
Q2 TRANSISTOR: NPN - OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	_	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	0.1	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	_	-	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	_	-	Vdc
DC Current Gain (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA)	h <sub>FE</sub>	80	140	-	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(SAT)</sub>	-	_	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, $V_B$ = 2.5 V, $R_L$ = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC}$ = 5.0 V, $V_B$ = 0.5 V, $R_L$ = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	_	-	Vdc
Input Resistor	R1	33	47	61	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	



#### TYPICAL ELECTRICAL CHARACTERISTICS - PNP TRANSISTOR

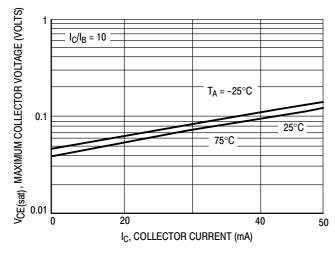


Figure 2. V<sub>CE(sat)</sub> versus I<sub>C</sub>

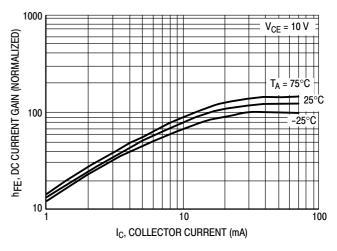


Figure 3. DC Current Gain

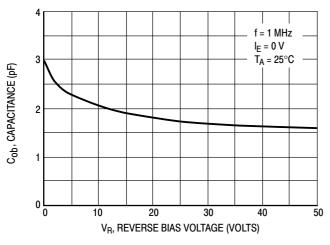


Figure 4. Output Capacitance

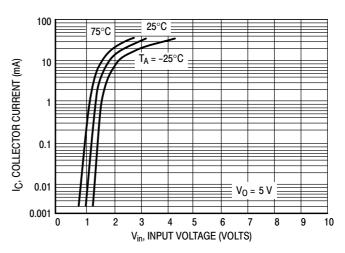


Figure 5. Output Current versus Input Voltage

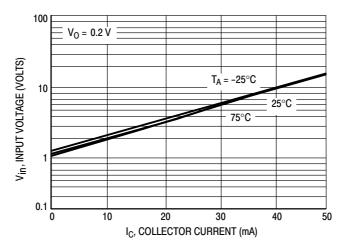


Figure 6. Input Voltage versus Output Current

#### TYPICAL ELECTRICAL CHARACTERISTICS — NPN TRANSISTOR

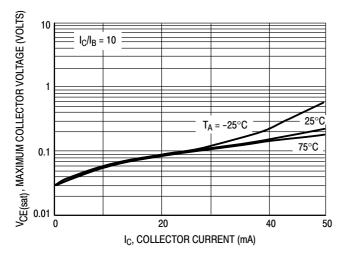


Figure 7. V<sub>CE(sat)</sub> versus I<sub>C</sub>

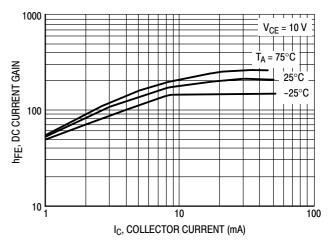


Figure 8. DC Current Gain

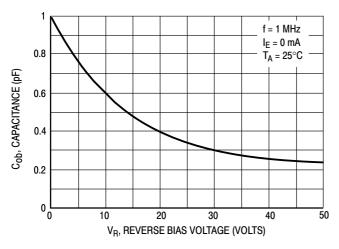


Figure 9. Output Capacitance

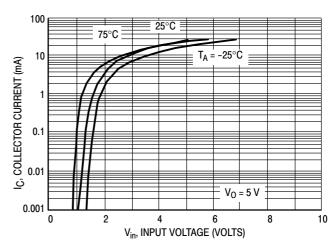


Figure 10. Output Current versus Input Voltage

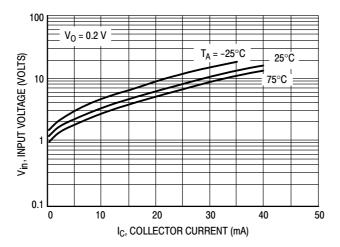
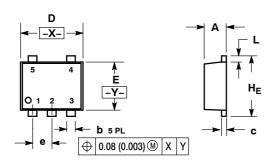


Figure 11. Input Voltage versus Output Current

#### **PACKAGE DIMENSIONS**

#### SOT-553 **XV5 SUFFIX** CASE 463B-01 **ISSUE B**

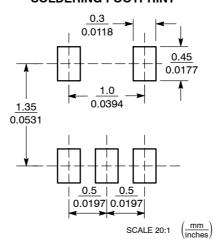


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES
  LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS

OF BASE MATERIAL

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.063	0.067
E	1.10	1.20	1.30	0.043	0.047	0.051
е		0.50 BSC			0.020 BS0	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.063	0.067

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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